ZnO COMPOUND SEMICONDUCTOR LIGHT EMITTING ELEMENT AND PRODUCTION METHOD THEREOF

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Inventor:

NIKI SHIGERU (JP); FONS PAUL (JP); IWATA KAKUYA

(JP); TANABE TETSUHIRO (JP); TAKASU HIDEMI (JP);

NAKAHARA KEN (JP)

Applicant:

JAPAN AS REPRESENTED BY SECRET (JP);; ROHM CO LTD (JP);; NIKI SHIGERU (JP);; FONS PAUL (JP);; IWATA KAKUYA (JP);; TANABE TETSUHIRO (JP);;

TAKASU HIDEMI (JP);; NAKAHARA KEN (JP)

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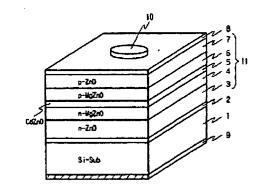
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Abstract of WO0108229

A silicon nitride film (2) is provided on a silicon substrate (1), and on the film (2) is laminated a semiconductor laminate (11) having at least ntype layers (3), (4) and p-type layers (6), (7) consisting of ZnO compound semiconductors so as to form a luminous layer. This silicon nitride film (2) is preferably formed by heat-treatment in an atmosphere containing nitrogen such as ammonia gas. In another embodiment, a luminous element or the like is formed by growing a ZnO compound semiconductor layer with a plane orthogonal to the C plane of a sapphire substrate used as a main plane, thereby providing a high-characteristic element using a ZnO compound such as an LED excellent in crystallinity and high in luminous efficiency.



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